

# GT0102 2-Bit Bidirectional Voltage-Level Translator

1 Features	2 Application
- No direction-control	- I2C/SMBus
- Data rates	- UART
24 Mbps (Push Pull),2 Mbps (Open Drain)	- GPIO
- 1.65 V to 3.6 V on A port and 2.3 V to 5.5 V on B port	
(V <sub>CCA</sub> ≤ V <sub>CCB</sub> )	
- $V_{cc}$ isolation feature: if either $V_{cc}$ input is at GND,	
both ports are in the high-impedance state	
- No power-supply sequencing required:	
either $V_{CCA}$ or $V_{CCB}$ can be ramped first	
- loff supports partial-power-down mode operation	
- Operating temperature range:-40°C to +85°C	

3 Description	Circuit diagram
This two-bit non-inverting translator which is a bidirectional voltage-level translator and can be used to build digital switching compatibility between multi voltage systems. This IC uses two separate configurable power supply tracks that including A ports supporting operating voltages from 1.65 V to 3.6 V with tracking VccA supply, and also including B ports supporting operating voltages from 2.3 V to 5.5 V with tracking VccB supply. The advantage above provides the support of both lower and higher logic signal levels while providing bidirectional translation capabilities between any of the 1.8-V, 2.5-V, 3.3-V, and 5- V voltage circuit points. Placing output-enable (OE) input to low level, all I/Os are forced to high-impedance state that significantly lower the quiescent current consumption. In order to ensure the high-impedance state during power up or power down, OE pin should be tied to GND via a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.	VCCA VCCB Processors Processors VCCB Peripherals



## **4 Revision History**

Revision	Date	Note
Rev. A1. 0	2023. 09. 21	Original Version
Rev. A1. 1	2023. 09. 09	Additional Switch Characteristics Data
Rev. A1. 2	2023. 10. 24	1.Update Package Qty 2.Added Tape and Reel Information
Rev. A1. 3	2023. 12. 18	Updated New Package
Rev. A1. 4	2024. 01. 26	Updated Part Name
Rev. A1. 5	2024. 07. 30	1.Updated Marking 2.Updated ESD

The latest datasheet version should be checked on the GTIC official website, as the company does not actively inform customers about updates to the datasheet.



## 5 Device Summary, Pin and Packages

Table 5-1. Device Summary<sup>(1)</sup>

Serial Name	Part Name	Package	Body Size (Nom)	Marking <sup>(2)</sup>	MSL <sup>(3)</sup>	Package Qty
GT0102	GT0102S8	SOT23-8	2.92mm×2.80mm	GT0102 XXXXX	3	Tape and Reel,3000
	GT0102D8	DFN-1.4×1-8L	1.40mm×1.00mm	0102 XXXX	3	Tape and Reel,5000
	GT0102V8	VSSOP8	2.00mm×2.30mm	0102 XXXX	3	Tape and Reel,3000

(1)For all available packages, please contact product sales.

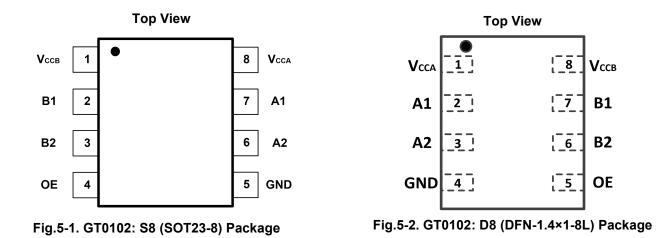
(2)There may be additional marking, which relates to the lot trace code information (data code and Vendor code), the logo or the environmental category on the device.

(3)MSL, The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications.

(4)"XXXXX" in Marking will be appeared as the batch code.



## 5 Device Summary, Pin and Packages(Continued)



F	Pin		VO	I/O	Function
Name	<b>S</b> 8	D8			
VCCB	1	8	-	B Port Supply Voltage. 2.3V≤V <sub>CCB</sub> .≤5.5V	
B1	2	7	I/O	Input/Output B1. Referenced to V <sub>CCB</sub> .	
B2	3	6	I/O	Input/Output B2. Referenced to V <sub>CCB</sub> .	
OE	4	5	I	Output Enable (Active High). Pull OE low to place all outputs in 3-state mode. Referenced to $$V_{\rm CCA}$.$	
GND	5	4	-	Ground	
A2	6	3	I/O	Input/Output A2. Referenced to V <sub>CCA</sub> .	
A1	7	2	I/O	Input/Output A1. Referenced to V <sub>CCA</sub> .	
VCCA	8	1	-	A Port Supply Voltage. 1.65V≤V <sub>CCA</sub> .≤3.6V and V <sub>CCA</sub> .≤V <sub>CCB</sub> .	

\*It is suggested to leave the unconnected pins floating.



## 5 Device Summary, Pin and Packages(Continued)

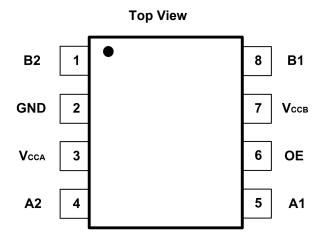


Fig.5-3. GT0102: V8 (VSSOP8) Package

#### Table 5-2 Pin Definition

Pin		I/O	Function		
Name	V8				
V <sub>CCB</sub>	7	Ρ	B Port Supply Voltage. 2.3V≤V <sub>CCB</sub> ≤5.5V		
B1	8	I/O	Input/Output B1. Referenced to V <sub>CCB.</sub>		
B2	1	I/O	Input/Output B2. Referenced to V <sub>CCB</sub> .		
OE	6	I	Output Enable(Active High). Pull OE low to place all outputs in 3-state mode. Referenced to $V_{CCA.}$		
GND	2	-	Ground		
A2	4	I/O	Input/Output A2. Referenced to V <sub>CCA.</sub>		
A1	5	I/O	Input/Output A1. Referenced to V <sub>CCA</sub> .		
V <sub>CCA</sub>	3	Ρ	A Port Supply Voltage. 1.65V≤V <sub>CCA</sub> ≤3.6V and V <sub>CCA</sub> ≤V <sub>CCB</sub>		

\* It is suggested to leave the unconnected pins floating.



### 6 Voltage, Temperature, ESD and Thermal Ratings

#### 6.1 Absolute Maximum Ratings<sup>(1)(2)(3)</sup>

Parameters	Min	Max	Unit	
Supply voltage, V <sub>CCA</sub>	-0.3	6.0	V	
Supply voltage, V <sub>CCB</sub>	-0.3	6.0	V	
	A port	-0.3	6.0	v
Input voltage range,V <sub>1</sub>	B port	-0.3	6.0	ľ
Voltage range applied to any output in the high-impedance or power-off	A port	-0.3	6.0	v
state, Vo	B port	-0.3	6.0	v
	A port	-0.3	V <sub>CCA</sub> +0.3	v
Voltage range applied to any output in the high or low state, Vo	B port	-0.3	V <sub>CCA</sub> +0.3	v
Input clamp current,I <sub>IK</sub>	VI<0		-50	mA
Output clamp current,I <sub>OK</sub>	VO<0		-50	mA
Continuous output current,Io			±50	mA
Continuous current through V <sub>CCA</sub> ,V <sub>CCB</sub> or GND		±100	mA	
Maximum junction temperature		150	°C	
Storage temperature range		-65	150	°C

(1)Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

(2)The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3)The value of  $V_{\mbox{\tiny CCA}}$  and  $V_{\mbox{\tiny CCB}}$  are provided in the recommended operating conditions table.

#### 6.2 ESD Ratings

	E	Value	Unit	
V(ESD) Electr	Electrostatic discharge	Human-Body Model (HBM)(1)	±6K	V
(200)		Charged-Device Model (CDM)(2)	±2K	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



### 6 Voltage, Temperature, ESD and Thermal Ratings(Continued)

#### 6.3 Recommended Operating Conditions

Vcci is the supply voltage associated with the input port.Vcco is the supply Voltage associated with the output port.

Parameter		Conditions	Min	Тур	Мах	Unit	
Supply voltage <sup>(1)</sup>		V <sub>CCA</sub>	1.65		3.6	V	
Supply voltage (		V <sub>CCB</sub>			5.5	v	
		V <sub>CCA</sub> =1.65 V to 1.95 V	V <sub>CCI</sub> -0.2		V <sub>CCI</sub>		
	A-port I/Os	$V_{CCB}$ =2.3 V to 5.5 V	VCC-0.2		VCCI		
		V <sub>CCA</sub> =2.3 V to 3.6 V	V <sub>CCI</sub> -0.4		Vool		
High-level		$V_{CCB}$ =2.3 V to 5.5 V	VCC-0.4		Vcci	V	
input voltage(Vін)	B-port I/Os	V <sub>CCA</sub> =1.65 V to 3.6V	Vcci-0.4		Vcci	v	
	B-port 1/OS	$V_{\rm CCB} \mbox{=} 2.3 \mbox{ V to } 5.5 \mbox{ V}$	VCCI-0.4		V CCI		
	OE input	V <sub>CCA</sub> =1.65 V to 3.6 V	V <sub>CCI</sub> ×0.8		5.5		
		$V_{CCB}$ =2.3 V to 5.5 V					
	A-port I/Os	V <sub>CCA</sub> =1.65 V to 1.95 V	0		0.15	V	
		$V_{CCB}$ =2.3 V to 5.5 V			0.15		
Low-level	B-port I/Os	V <sub>CCA=</sub> 1.65 V to 3.6 V	0		0.15	v	
input voltage(V <sub>IL</sub> ) <sup>(2)</sup>	D-poit 1/03	$V_{CCB}$ =2.3 V to 5.5 V	Ŭ		0.10		
	OE input	V <sub>CCA</sub> =1.65 V to 3.6 V	0		V <sub>CCA</sub> ×0.25	V	
		$V_{CCB}$ =2.3 V to 5.5 V	Ŭ		• CCA / CO. 20		
Input transition rise	A-port I/0	Os push-pull driving			10		
or fall rate( $\Delta t/\Delta v$ )	B-port I/Os push-pull driving				10	ns/∖	
	Control input				10		
TA operating free-air					85	°C	
temperature			-40			0	

(1)  $V_{CCA}$  must be less than or equal to  $V_{CCB}$ .

(2) The maximum  $V_{IL}$  value is provided to ensure that a valid  $V_{OL}$  is maintained. The  $V_{OL}$  value is  $V_{IL}$  plus the voltage drop across the pass gate transistor.



## **7 Electrical Specifications**

#### 7.1 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)  $^{(1)(2)(3)}$ 

		•								
Ра	rameter	Conditions	Vcca	Vccв	Temp	Min	Тур	Max	Unit	
Voha	Port A Output High Voltage	I <sub>OH</sub> =–20 μA V <sub>IB</sub> ≥ V <sub>CCB</sub> – 0.4V	1.65V to 3.6V	2.3V to 5.5V	Full	V <sub>CCA</sub> ×0.7			V	
Vola	Port A Output Low Voltage	I <sub>OL</sub> =1mA V <sub>IB</sub> ≤ 0.15 V	1.65V to 3.6V	2.3V to 5.5V	Full			0.3	V	
V <sub>OHB</sub>	Port B Output High Voltage	I <sub>OH</sub> =−20 μA V <sub>IA</sub> ≥ V <sub>CCA</sub> − 0.4V	1.65V to 3.6V	2.3V to 5.5V	Full	$V_{CCA}  imes 0.7$			V	
V <sub>OLB</sub>	Port B Output Low Voltage	I <sub>OL</sub> =1mA V <sub>IA</sub> ≤ 0.15 V	1.65V to 3.6V	2.3V to 5.5V	Full			0.3	V	
h	Input Leakage	OE	1.65V to 3.6V	2.3V to 5.5V	<b>+25</b> ℃			±1	μA	
II	Current	UE	1.05 10 5.0 1	2.30 10 5.50	Full			±1.5	μΑ	
		A Ports	0V	0V to 5.5V	<b>+25</b> ℃			±0.5		
I <sub>off</sub>	Partial Power	AFOIIS	00	00 10 5.50	Full			±1	μA	
lott	Down Current	Current	0V to 3.6V	οv	<b>+25</b> ℃			±0.5	μΑ	
		DFOILS	00 10 3.00	00	Full			±1		
loz	High-impedance State Output	A or B port	1.65V to 3.6V	2.3V to 5.5V	<b>+25</b> ℃			±0.5	5 μΑ	
102	Current	OE=0V	1.007 10 0.07	2.57 10 5.57	Full			±1		
			1.65V to V <sub>CCB</sub>	2.3v to 5.5V	Full			2.5		
ICCA	V <sub>CCA</sub> Supply Current	V <sub>I</sub> =V <sub>O</sub> =open I <sub>O</sub> =0	3.6v	0V	Full			2.5	μA	
			0v	5.5V	Full			-1		
			1.65V to V <sub>CCB</sub>	2.3v to 5.5V	Full			10		
I <sub>CCB</sub>	V <sub>CCB</sub> Supply Current	V <sub>I=</sub> V <sub>O</sub> =open I <sub>O</sub> =0	3.6v	0V	Full			-1	μA	
			0v	5.5V	Full			1		
I <sub>CCA</sub> + I <sub>CCB</sub>	Combined Supply Current	$V_I = V_{CCI}$ or GND $I_{O=0}$	1.65V to V <sub>CCB</sub>	2.3v to 5.5V	Full			13	μA	
I <sub>CCZA</sub>	V <sub>CCA</sub> Supply Current	V <sub>I</sub> =V <sub>CCI</sub> or 0V I <sub>O</sub> =0, OE=0V	1.65V to V <sub>CCB</sub>	2.3v to 5.5V	Full			1	μA	
I <sub>CCZB</sub>	V <sub>CCB</sub> Supply Current	V <sub>I</sub> =V <sub>CCI</sub> or 0V I <sub>O=</sub> 0, OE=0V	2.3v to 3.6V	2.3v to 5.5V	Full			1	μA	
Ci	Input Capacitance	OE	3.3V	3.3V	<b>+25</b> ℃		2.5		PF	
Cio	Input-to-output Internal	A Port	3.3V	3.3V	<b>+25</b> ℃		5		PF	
0.0	Capacitance	B Port	3.3V	3.3V	<b>+25</b> ℃		5			

(1)  $V_{\text{CCI}}$  is the  $V_{\text{CC}}$  associated with the input port.

(2)  $V_{\text{CCO}}$  is the  $V_{\text{CC}}$  associated with the output port

(3)  $V_{\text{CCA}}$  must be less than or equal to  $V_{\text{CCB}}.$ 



### 7.2 Timing Requirements

#### $V_{\text{CCA}}\text{=}1.8V{\pm}0.15V$

		V <sub>CCB</sub> =2.5V±0.2V	V <sub>CCB</sub> =3.3V±0.2V	V <sub>CCB</sub> =5V±0.2V	Unit
		Тур	Тур	Тур	Unit
Data Rate	Push-pull Driving	21	22	24	Mhno
	Open-drain Driving	2	2	2	Mbps
Pulse Duration(tw)	Push-pull Driving (Data Inputs)	47	45	41	
	Open-drain Driving (Data Inputs)	500	500	500	ns

#### $V_{\text{CCA}}\text{=}2.5V{\pm}0.15V$

		V <sub>CCB</sub> =2.5V±0.2V	V <sub>CCB</sub> =3.3V±0.2V	V <sub>CCB</sub> =5V±0.2V	Unit
		Тур	Тур	Тур	Unit
Data Rate -	Push-pull Driving	20	22	24	Maria
	Open-drain Driving	2	2	2	Mbps
Pulse Duration(tw)	Push-pull Driving (Data Inputs)	50	45	41	
	Open-drain Driving (Data Inputs)	500	500	500	ns

#### $V_{\text{CCA}}\text{=}3.3V{\pm}0.15V$

		V <sub>ссв</sub> =3.3V±0.2V	V <sub>ссв</sub> =5V±0.2V	Unit	
		Тур	Тур	Unit	
Data Rate —	Push-pull Driving	Push-pull Driving 23		Mhoo	
	Open-drain Driving	2	2	Mbps	
Pulse Duration(tw)	Push-pull Driving (Data Inputs)	43	41	20	
	Open-drain Driving (Data Inputs)	500	500	ns	

#### 7.3 Switching Characteristics: $V_{CCA}$ =1.8V $\pm$ 0.15V

over recommended operating free-air temperature range (unless otherwise noted)

<b>P</b>				$V_{ccB}$ =2.5V $\pm$ 0.2V	V <sub>ccB</sub> =3.3V±0.2V	$V_{ccB}$ =5V $\pm$ 0.2V		
	Parameter		Conditions	Тур	Тур	Тур	Units	
tрнL	Propagation Delay Time	A to B	Push-pull Driving	5.6	5	5	ns	
UP IIL	High-to-low Output	7.00	Open-drain Driving	7.5	7.9	8.3	113	
t=	Propagation Delay Time low-to-high Output	A to B	Push-pull Driving	10.0	9.5	9	ns	
UPLH		AIOB	Open-drain Driving	181	170	154	115	
tрнL	Propagation Delay Time	B to A	Push-pull Driving	7	7.1	7.2		
UT TIL	High-to-low Output	BIOA	Open-drain Driving	7.6	8.1	9.2	ns	
t <sub>рін</sub>	Propagation Delay Time	B to A	Push-pull Driving	7.6	6.9	6	ns	
4 EII	low-to-high Output		Open-drain Driving	163	145	118		
t <sub>en</sub>	Enable Time	OE to A or B		135	159	182	ns	
t <sub>dis</sub>	Disable Time		OE to A or B	170	174	181	ns	
t <sub>rA</sub>	Input Rise Time	A port	Push-pull Driving	13.4	11.9	10.6	ns	
۲A		rise time	Open-drain Driving	68	66	62	115	
t <sub>rв</sub>	Input Rise Time	B port	Push-pull Driving	13	12	11.6	ns	
чв		rise time	Open-drain Driving	66	65	50	110	
t <sub>fA</sub>	Input Fall Time	A port fall	Push-pull Driving	5.6	4.7	4.0	ns	
4A		time	Open-drain Driving	5.0	5.1	5.2	110	
t <sub>fB</sub>	Input Fall Time	B port fall	Push-pull Driving	3.0	3.0	2.9	ns	
40		time	Open-drain Driving	6.1	5.6	4.4		
t <sub>sk(o)</sub>	Skew(time), Output	Channel-to-Channel Skew		0.5	0.5	0.5	ns	
Ma	ximum Data Rate		Push-pull Driving	22	23	24	Mbps	
			Open-drain Driving		2	2	IVIDH2	

### 7.4 Switching Characteristics, V\_{CCA}=2.5V $\pm 0.15V$

over operating free-air temperature range (unless otherwise noted)

Demonster		Oppditions		V <sub>ccB</sub> =2.5V±0.2V	V <sub>ccB</sub> =3.3V±0.2V	$V_{ccB}$ =5V $\pm$ 0.2V	11	
	Parameter		Conditions	Тур	Тур	Тур	Units	
tрнL	Propagation Delay Time	A to B	Push-pull Driving	3.5	3.5	3.2	20	
LPHL	High-to-low Output	AIUB	Open-drain Driving	6.3	6.5	6.7	ns	
	Propagation Delay Time low-to-high Output	A to B	Push-pull Driving	4.5	4.9	4.7		
tрін		AIOB	Open-drain Driving	158	152	142	ns	
t <sub>PHL</sub>	Propagation Delay Time	B to A	Push-pull Driving	3.7	3.9	4.6		
(PHL	High-to-low Output	DIOA	Open-drain Driving	6	6.6	7.7	ns	
t <sub>PLH</sub>	Propagation Delay Time	B to A	Push-pull Driving	4.8	4	2.5	ns	
ΨLH	low-to-high Output		Open-drain Driving	153	138	116	113	
t <sub>en</sub>	Enable Time	OE to A or B		7.7	41.8	130	ns	
t <sub>dis</sub>	Disable Time		OE to A or B	175	181	182	ns	
t <sub>rA</sub>	Input Rise Time	A port	Push-pull Driving	9.8	8.6	7.5	ns	
ча		Rise Time	Open-drain Driving	79	77	65	110	
4	Innut Dice Time	B port	Push-pull Driving	9.8	8.7	8.1	20	
trв	Input Rise Time	Rise Time	Open-drain Driving	93	68	53	ns	
t <sub>fA</sub>	Input Fall Time	A port Fall	Push-pull Driving	4.6	4.1	3.6	ns	
ЧfА		Time	Open-drain Driving	5.1	5.1	5.2	115	
t <sub>fB</sub>	Input Fall Time	B port Fall	Push-pull Driving	4.5	4.0	4.0	ns	
чВ		Time			7.4	7.8	115	
t <sub>sκ(o)</sub>	Skew(time), Output	Cha	annel-to-Channel Skew	0.5	0.5	0.5	ns	
Ма	ximum Data Rate	Push-pull Driving		22	24	24	Mbps	
ivia			Open-drain Driving		2	2	wops	

### 7.5 Switching Characteristics, V\_{CCA}=3.3V $\pm 0.3V$

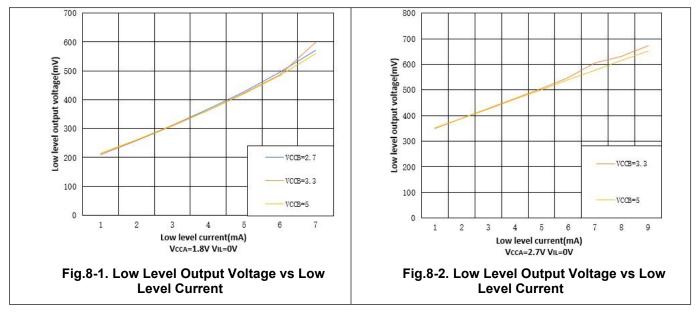
over recommended operating free-air temperature range (unless otherwise noted)

	1 0		• •	,			
Parameter			Conditions		$V_{ccB}$ =5V $\pm$ 0.2V	Units	
	Parameter		Conditions	ТҮР	ТҮР	Units	
<b>t</b>	Propagation Delay Time	A to B	Push-pull Driving	2.1	2.2	20	
tph∟	High-to-low Output	A to B	Open-drain Driving	5.9	6.1	ns	
	Propagation Delay Time		Push-pull Driving	1	3.3		
tршн	High-to-low Output	A to B	Open-drain Driving	138	131	ns	
4	Propagation Delay Time		Push-pull Driving	2.3	2.6		
t <sub>PHL</sub>	High-to-low Output	B to A	Open-drain Driving	5.4	6.6	ns	
t <sub>PLH</sub>	Propagation delay time	B to A	Push-pull Driving	1.0	1.0	ns	
	low-to-high Output		Open-drain Driving	133	115		
t <sub>en</sub>	Enable Time		OE to A or B	4.7	5.2	ns	
t <sub>dis</sub>	Disable Time		OE to A or B	174	182	ns	
t <sub>rA</sub>	Input Rise Time	A port	Push-pull Driving	7.4	6.6	ns	
۲A		Rise Time	Open-drain Driving	75	67	115	
t <sub>rв</sub>	Input Rise Time	B port	Push-pull Driving	7.7	7.1	ns	
ιrΒ		Rise Time	Open-drain Driving	70	65	115	
t <sub>fA</sub>	Input Fall Time	A port Fall	Push-pull Driving	3.4	3.0	ns	
чA		Time	Open-drain Driving	5.1	5.1	115	
t <sub>fB</sub>	Input Fall Time	B port Fall	Push-pull Driving	3.5	3.2	ns	
чВ			Time Open-drain Driving		6.7		
t <sub>sk(0)</sub>	Skew(time), Output	C	hannel-to-Channel Skew	0.5	0.5	ns	
М	aximum Data Rate		Push-pull Driving	24	24	Mbps	
			Open-drain Driving	2	2		





# **8 Typical Characteristics**





### 9 Parameter Measurement Information

Unless otherwise noted, all input pulsed are supplied by generators having the following characteristics:

- PSRR 10MHz
- Zo=50 Ω
- $dv/dt \ge 1V/ns$

Note: All input pulses are measured one at a time with one transition per measurement

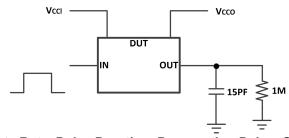


Fig.9-1. Data Rate, Pulse Duration, Propagation Delay, Output Rise and Fall Time Measurement Using a Push-Pull Driver

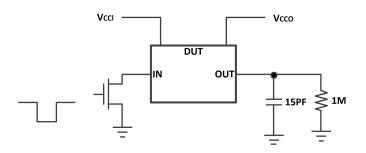


Fig.9-2. Data Rate, Pulse Duration, Propagation Delay, Output Rise and Fall Time Measurement Using an Open-Drain Driver

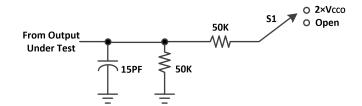


Fig.9-3. Load Circuit for Enable/Disable Time Measurement Table 9-1 Switch Configuration for Enable/Disable Timing

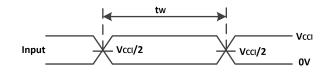
Test	S1
t <sub>PZL</sub> <sup>(1)</sup> , t <sub>PLZ</sub> <sup>(2)</sup>	2×V <sub>cco</sub>
t <sub>PHZL</sub> <sup>(1)</sup> , t <sub>PZH</sub> <sup>(2)</sup>	Open

(1)  $t_{\text{PZL}}$  and  $t_{\text{PZH}}$  are the same as ten.

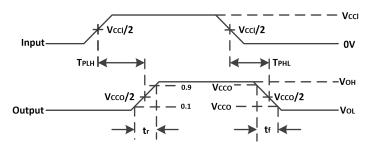
(2)  $t_{PLZ}$  and  $t_{PHZ}$  are the same as tdis.

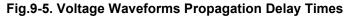


### 9 Parameter Measurement Information(Continued)



(1) All input pulses are measured one at a time, with one transition per measurement. Fig.9-4. Voltage Waveforms Pulse Duration





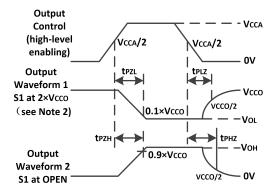


Fig.9-6. Voltage Waveforms Enable and Disable



### **10 Detailed Description**

#### 10.1 Overview

The GT0102 IC is a Bi-direction voltage-level translator specifically designed for translating logic voltage levels. The A port can accept I/O voltages that cover from 1.65 V to 3.6 V range; The B port can accept I/O voltages from 2.3 V to 5.5 V. The device is a pass-gate architecture with edge-rate accelerators (one-shots) to improve the overall data rate. 10-k $\Omega$  pullup resistors that usually used in open-drain applications have been integrated inside IC with the advantage saving an external resistor. Not only the IC is designed for open-drain applications, but also this device can translate push-pull CMOS logic outputs.

#### **10.2 Architecture**

The GT0102 architecture (see Figure below) is a translator with Bi-direction-Sensing function that means a directioncontrol mechanism to control the direction of data flow from A to B or from B to A is not needed. These two bidirectional channels independently determine the direction of data flow without a direction-control signal. This autodirection feature is realized by each I/O pin can be automatically reconfigured as either an input or an output.

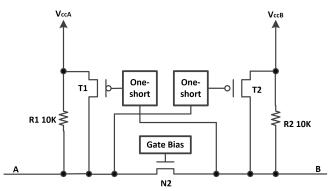


Fig.10-1. Architecture of GT0102



### **11 Application Information**

The GT0102 device can be used to bridge the digital-switching compatibility gap between two voltage nodes to successfully interface logic threshold levels found in electronic systems. It should be used in a point-to-point topology for interfacing devices or systems operating at different interface voltages with one another. Its primary target application use is for interfacing with open-drain drivers on the data I/Os such as I2C or 1-wire, where the data is bidirectional and no control signal is available. The device can also be used in applications where a push-pull driver is connected to the data I/Os, but the GT0102 might be a better option for such push-pull applications.

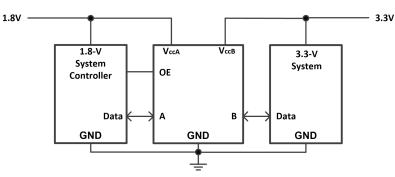
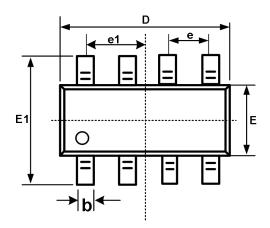


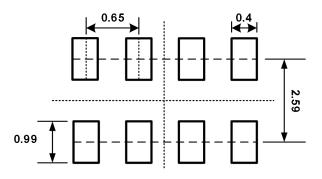
Fig.11-1. Typical Application Schematic



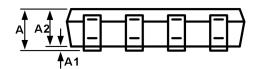
## 12 Package Outline Dimension

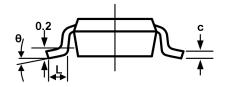
SOT23-8





Recommended Land Pattern (Unit: mm)



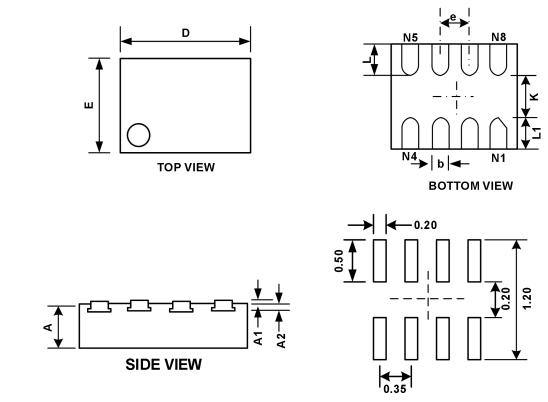


Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
Cymbol	Min	Мах	Min	Мах		
A	1.050	1.250	0.041	0.049		
A1	0.000	0.100	0.000	0.004		
A2	1.050	1.150	0.041	0.045		
b	0.300	0.500	0.012	0.020		
С	0.100	0.200	0.004	0.008		
D	2.820	3.020	0.111	0.119		
E	1.500	1.700	0.059	0.067		
E1	2.650	2.950	0.104	0.116		
е	0.650	BSC	0.026BSC			
e1	0.975BSC		0.038	BSC		
L	0.300	0.600	0.012	0.024		
θ	0°	8°	0°	8°		



# 12 Package Outline Dimension(Continued)

DFN1.4×1-8L



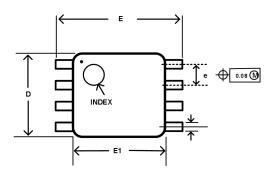
**RECOMMENDED LAND PATTERN (Unit:mm)** 

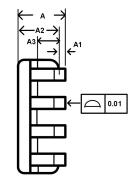
Symbol	Dimensions i	in Millimeters	Dimensions in Inches			
Cymson	Min	Мах	Min	Max		
A	0.340	0.400	0.013	0.016		
A1	0.000	0.050	0.000	0.002		
A2	0.110	DREF	0.004REF			
D	1.350	1.450	0.053	0.057		
E	0.950	1.050	0.037	0.041		
k	0.200	OMIN	0.008MIN			
b	0.150	0.200	0.006	0.008		
е	0.350TYP		0.014	14TYP		
L	0.250	0.350	0.010	0.014		
L1	0.350	0.450	0.014	0.018		

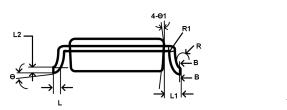


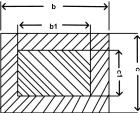
# 12 Package Outline Dimension(Continued)

### VSSOP8





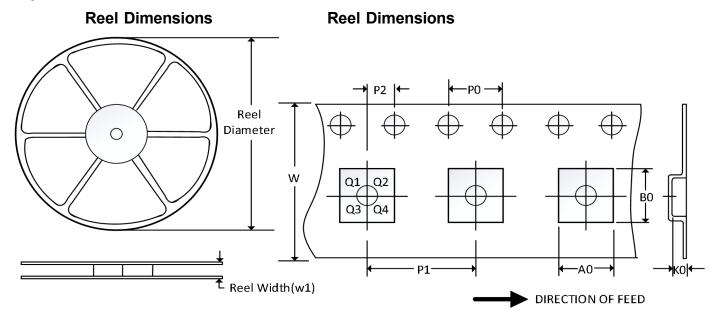




Symbol	Din	nensions in Millin	neters	Dimensions in Inches				
Cymson	Min	Nom	Max	Min	Nom	Max		
A	-	-	0.90	-	-	0.035		
A1	0	0.05	0.10	0.000	0.002	0.004		
A2	0.65	0.75	0.80	0.026	0.030	0.031		
A3	0.32	0.37	0.42	0.013	0.015	0.017		
b	0.17	-	0.27	0.007	-	0.011		
b1	0.17	0.20	0.23	0.007	0.008	0.009		
С	0.10	-	0.18	0.004	-	0.007		
c1	0.10	0.13	0.14	0.004	0.005	0.006		
D	1.90	2.00	2.10	0.075	0.079	0.083		
E	3.00	3.10	3.20	0.118	0.122	0.126		
E1	2.20	2.30	2.40	0.087	0.091	0.094		
е	0.40	0.50	0.60	0.016	0.020	0.024		
L	0.20	0.26	0.35	0.008	0.010	0.014		
L1		0.40REF			0.016REF			
L2		0.12BSC			0.005BSC			
R	0.07	-	-	0.003	-	-		
R1	0.07	-	-	0.003	-	-		
θ	0°	-	6°	0°	-	6°		
θ1	9°	12°	15°	9°	12°	15°		



# 13 Tape and Reel Information



Note: The picture is only for reference. Please make the object as the standard.

#### Key Parameter List of Tape and Reel

Deelesse Tures	De al Diamatan		A0	B0	K0	P0	P1	P2	W	Pin1
Package Type	Reel Diameter	Reel Width (mm)	Quadrant							
SOT23-8	7"	9.5	3.17	3.23	1.37	4.0	4.0	2.0	8.0	Q3
DFN1.4*1.0-8L	7"	9.5	1.2	1.6	0.5	4.0	4.0	2.0	8.0	Q1
VSSOP8	7"	9.5	2.25	3.35	1.40	4.0	4.0	2.0	8.0	Q3

Note:

(1)All dimensions are nominal.
(2)Plastic or metal protrusions of 0.15mm maximum per side are not included.